

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	I_D $T_A = +25^\circ\text{C}$
100V	220m Ω @ $V_{GS} = 10\text{V}$	1.6A
	250m Ω @ $V_{GS} = 4.5\text{V}$	1.3A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

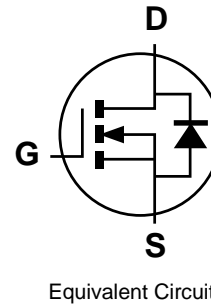
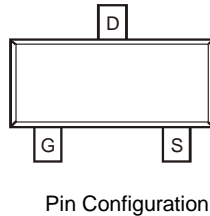
- Load Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.0072 grams (approximate)



Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220L-7	Standard	SOT23	3,000/Tape & Reel
DMN10H220L-13	Standard	SOT23	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N1H = Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or \bar{Y} = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019
Code	A	B	C	D	E	F	G

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±16	V
Continuous Drain Current (Note 5) V _{GS} = 10V	(Note 6) T _A = +25°C T _A = +70°C	1.6 1.3	A
	(Note 5) T _A = +25°C T _A = +70°C	1.4 1.1	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	0.6	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	8	A

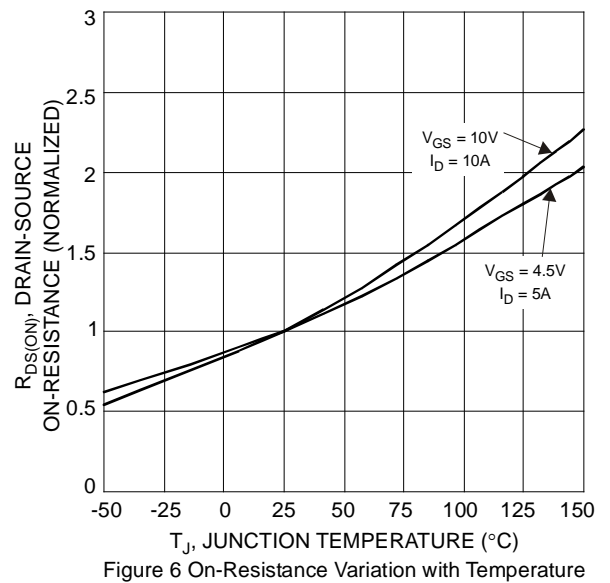
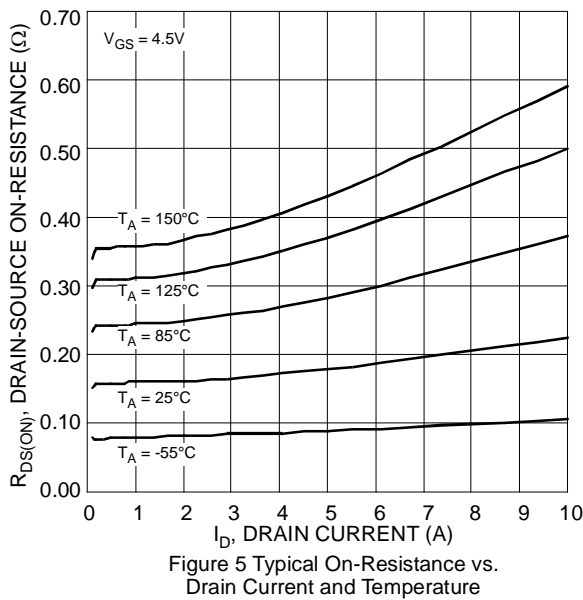
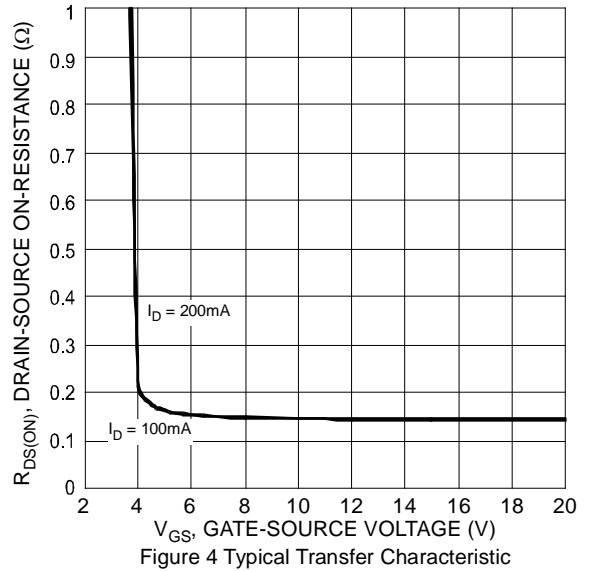
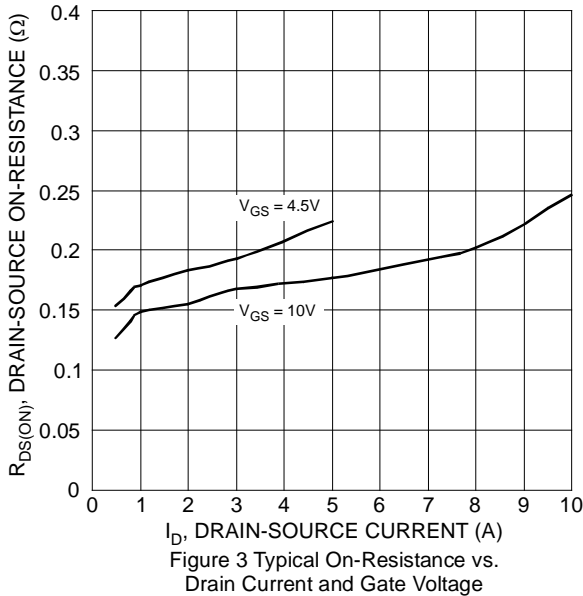
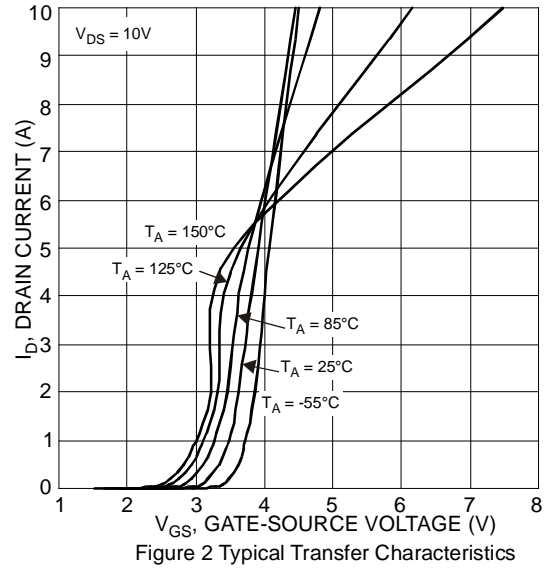
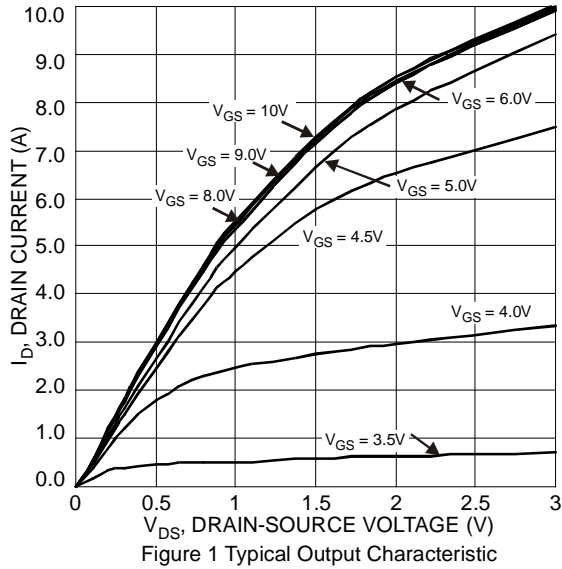
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	1.3
		T _A = +70°C	0.8
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 6)	94
		(Note 5)	177
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	220	mΩ	V _{GS} = 10V, I _D = 1.6A
		—	—	250		V _{GS} = 4.5V, I _D = 1.3A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	401	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	22	—		
Reverse Transfer Capacitance	C _{rss}	—	17	—		
Gate Resistance	R _g	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.1	—	nC	V _{DS} = 50V, I _D = 1.6A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	8.3	—		
Gate-Source Charge	Q _{gs}	—	1.5	—		
Gate-Drain Charge	Q _{gd}	—	2	—		
Turn-On Delay Time	t _{D(on)}	—	6.8	—	ns	V _{DS} = 50V, V _{GS} = 4.5V, R _G = 6.8Ω, I _D = 1A
Turn-On Rise Time	t _r	—	8.2	—		
Turn-Off Delay Time	t _{D(off)}	—	7.9	—		
Turn-Off Fall Time	t _f	—	3.6	—		
Reverse Recovery Time	t _{rr}	—	17	—	ns	I _F = 1.1A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{rr}	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



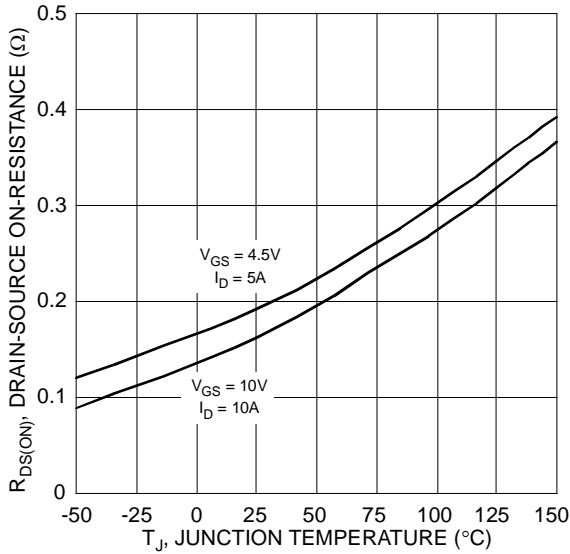


Figure 7 On-Resistance Variation with Temperature

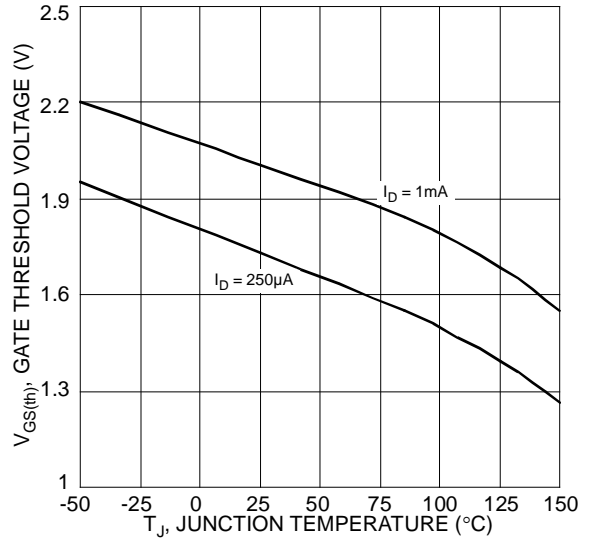


Figure 8 Gate Threshold Variation vs. Ambient Temperature

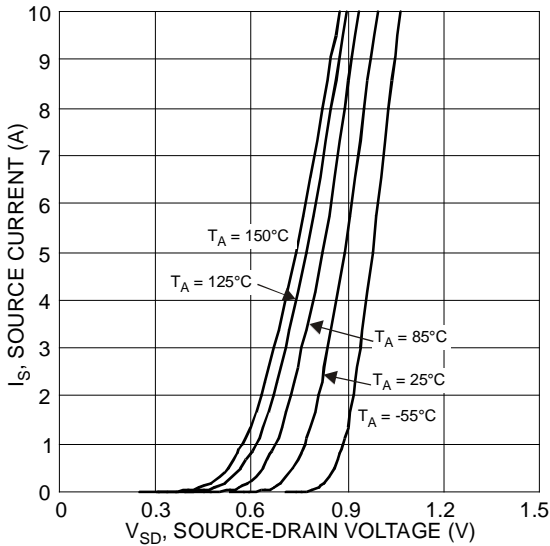


Figure 9 Diode Forward Voltage vs. Current

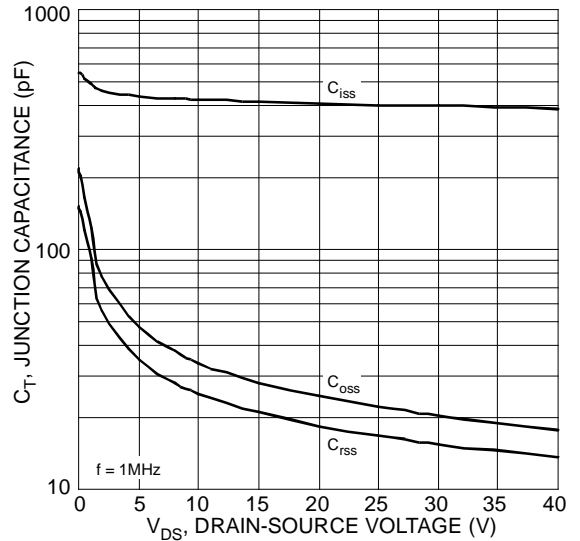


Figure 10 Typical Junction Capacitance

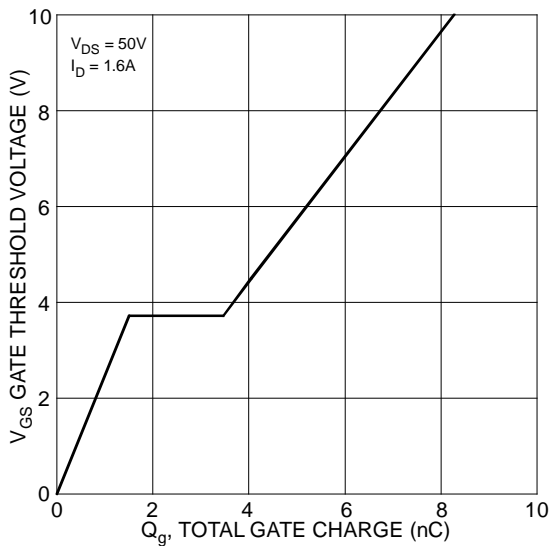


Figure 11 Gate Charge

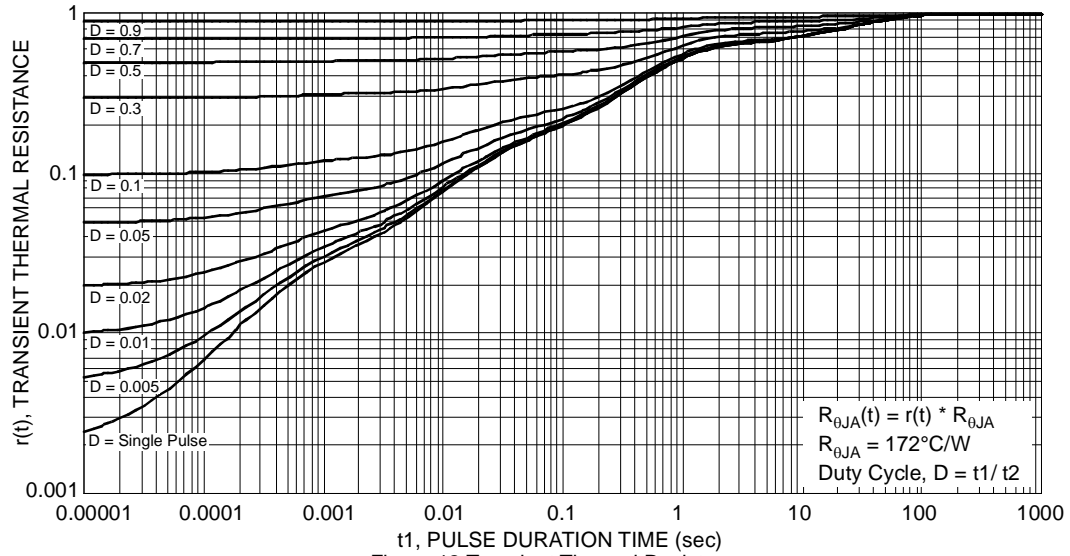
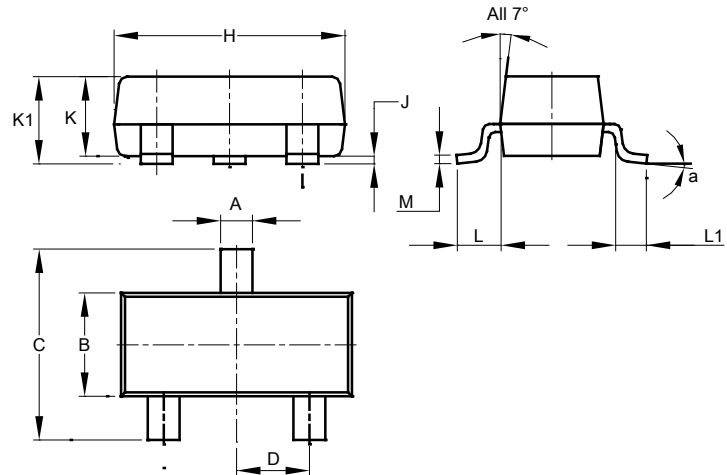


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

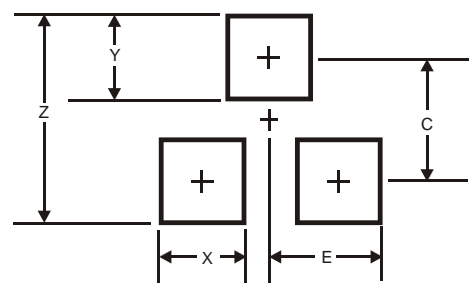
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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